TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7WG125FC

Dual Bus Buffer with 3-STATE Output

Features

• High-level output current: $I_{OH}/I_{OL} = \pm 8 \text{ mA (min)}$

at $V_{CC} = 3 V$

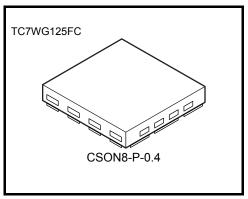
• High-speed operation: $t_{pd} = 2.5 \text{ ns (typ.)}$

at $V_{CC} = 3.3 \text{ V}, 15 \text{pF}$

• Operating voltage range: V_{CC} = 0.9~3.6 V

• 5.5-V tolerant inputs

• 3.6-V power down protection outputs



Weight: 0.002 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Value	Unit	
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	V _{IN}	-0.5~7.0	V	
DC output voltage	V	-0.5~4.6 (Note 1)	V	
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5 (Note 2)	V	
Input diode current	I _{IK}	-20	mA	
Output diode current	lok	-20 (Note 3)	mA	
DC output current	lout	±25	mA	
DC V _{CC} /GND current	Icc	±100	mA	
Power dissipation	PD	150 (Note 4)	mW	
Storage temperature	T _{stg}	-65~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: V_{CC} = 0 V

Note 2: High or Low State.

I_{OUT} absolute maximum rating must be observed.

Note 3: V_{OUT} < GND

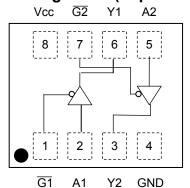
Note 4: Mounted on an FR4 board.

 $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ t}, \text{ Cu Pad: } 11.56 \text{ mm}^2)$

Marking

G125

Pin Assignment (top view)

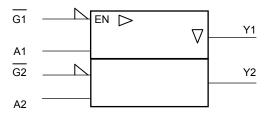


Truth Table

Inp	Outputs	
G	А	Υ
Н	Χ	Z
L	L	L
L	Н	Н

X: Don't Care Z: High impedance

IEC Logic Symbol



Operating Ranges

Characteristics	Symbol	Value	Unit	
Power supply voltage	V _{CC}	0.9~3.6	V	
Input voltage	V _{IN}	0~5.5	V	
Output valtage	V	0~3.6 (Note 5)	V	
Output voltage	V _{OUT}	0~V _{CC} (Note 6)	V	
		±8.0 (Note 7)		
		±4.0 (Note 8)		
Output Course		±3.0 (Note 9)	A	
Output Current	I _{OH} /I _{OL}	±1.7 (Note 10)	mA	
		±0.3 (Note 11)		
		±0.02 (Note 12)		
Operating temperature	T _{opr}	−40 ~ 85	°C	
Input rise and fall time	dt/dV	0~10 (Note 13)	ns/V	

Note 5: $V_{CC} = 0 V$

Note 6: High or Low state.

Note 7: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note 8: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 9: $V_{CC} = 1.65 \sim 1.95 \text{ V}$

Note 10: $V_{CC} = 1.4 \sim 1.6 \text{ V}$

Note 11: $V_{CC} = 1.1 \sim 1.3 \text{ V}$

Note 12: $V_{CC} = 0.9 \text{ V}$

Note 13: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$

Electrical Characteristics

DC Characteristics

Characteristics		Symbol	Tool	Condition		-	Га = 25°C)	Ta = -4	0~85°C	Unit					
Ondractonation		Syllibol	bol Test Condition		V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic					
					0.9	V _C C	_	_	V _{CC}	_						
					1.1~1.3	V _{CC} × 0.7	_	_	V _{CC} × 0.7	_						
	High level	V _{IH}		_		V _{CC} × 0.65	_	_	V _{CC} × 0.65	_						
					1.65~ 1.95	V _{CC} × 0.65	_	_	V _{CC} × 0.65	_						
					2.3~2.7	1.7			1.7	_						
Input voltage					3.0~3.6	2.0			2.0	_	V					
input voitage					0.9	_	_	GND	_	GND	V					
					1.1~1.3	_	_	V _{CC} × 0.3	_	V _{CC} × 0.3						
	Low level	V _{IL}		_	1.4~1.6	_	_	V _{CC} × 0.35	_	V _{CC} × 0.35						
					1.65~ 1.95	_	_	V _{CC} × 0.35	_	V _{CC} × 0.35						
					2.3~2.7	_	_	0.7	_	0.7						
										3.0~3.6	_	_	0.8	_	0.8	
		n level V _{OH}			I _{OH} =-0.02 mA	0.9	0.75	_	_	0.75	_					
	High level V ₀			$I_{OH} = -0.3 \text{ mA}$	1.1~1.3	V _{CC} × 0.75	_	_	V _{CC} × 0.75							
			V _{IN} =V _{IL} or V _{IH}	$I_{OH} = -1.7 \text{ mA}$	1.4~1.6	V _{CC} × 0.75	_	_	V _{CC} × 0.75	_						
				$I_{OH} = -3.0 \text{ mA}$	1.65~ 1.95	V _{CC} -0.45			V _{CC} -0.45	_						
				$I_{OH} = -4.0 \text{ mA}$	2.3~2.7	2.0			2.0]					
Output voltage				$I_{OH} = -8.0 \text{ mA}$	3.0~3.6	2.48	_	_	2.48	_	V					
Output Voltage				$I_{OL} = 0.02 \text{ mA}$	0.9	_	_	0.1	_	0.1	v					
				$I_{OL} = 0.3 \text{ mA}$	1.1~1.3	_		V _{CC} × 0.25	_	V _{CC} × 0.25						
	Low level	V _{OL}	V _{IN} = V _{IL}	I _{OL} = 1.7 mA	1.4~1.6	_	l	V _{CC} × 0.25	_	V _{CC} × 0.25						
				I _{OL} = 3.0 mA	1.65~ 1.95	_		0.45	_	0.45						
				I _{OL} = 4.0 mA	2.3~2.7	_	_	0.4	_	0.4						
				I _{OL} = 8.0 mA	3.0~3.6	_	_	0.4	_	0.4						
Input leakage current I		I _{IN}	V _{IN} = 0~5.5V		0~3.6		_	±0.1		±1.0	μА					
3-state output off-s	state current	I _{OZ}	V _{IN} = V _{IH} V _{OUT} = 0	or V _{IL} ~3.6V	0.9~3.6	_	_	1.0	_	10.0	μА					
Power off leakage	current	l _{OFF}	V _{IN} = 5.5\ or V _{OUT} =	V = 3.6V	0.0	_		1.0	_	10.0	μА					
Quiescent supply of	current	Icc	$V_{IN} = V_{CO}$	or GND	3.6	_	_	1.0	_	10.0	μА					

AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition			Га = 25°(Ta = -4	0~85°C	Unit
Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Тур.	Max	Min	Max	Oill
			0.9	_	18.3	_	_	_	
			1.1~1.3	_	9.4	18.4	1.0	34.9	
		C _L = 10 pF,	1.4~1.6	_	5.5	8.5	1.0	10.7	
		$R_L = 1 M\Omega$	1.65~ 1.95	_	4.2	6.2	1.0	6.7	
			2.3~2.7	_	2.8	3.9	1.0	4.4	
			3.0~3.6	_	2.3	3.1	1.0	3.7	
			0.9		21.2	_	_	_	
			1.1~1.3	_	10.7	21.5	1.0	38.0	
Propagation delay time	t _{pLH}	C _L = 15 pF,	1.4~1.6	_	6.1	9.3	1.0	11.9	ns
Fropagation delay time	t_{pHL}	$R_L = 1 M\Omega$	1.65~ 1.95	_	4.7	6.9	1.0	7.1	115
			2.3~2.7	_	3.1	4.4	1.0	5.0	
			3.0~3.6	_	2.5	3.4	1.0	3.9	
			0.9	_	30.5	_	_	_	
		$C_L=30$ pF, $R_L=1$ M Ω	1.1~1.3		14.9	30.0	1.0	58.1	
			1.4~1.6		8.2	13.2	1.0	16.6	
			1.65~ 1.95		6.1	9.2	1.0	9.9	
			2.3~2.7		4.1	5.7	1.0	6.1	
			3.0~3.6		3.4	4.4	1.0	4.8	
		$C_L = 10 \text{ pF},$ $R_L = 100 \text{ k}\Omega$ $C_L = 10 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	0.9		24.0	_	_	_	
			1.1~1.3	_	11.8	22.5	1.0	35.8	
			1.4~1.6		6.8	10.4	1.0	12.0	-
			1.65~ 1.95		5.1	7.3	1.0	8.1	
			2.3~2.7	1	3.4	4.6	1.0	5.3	
			3.0~3.6		2.5	3.4	1.0	3.9	
		$\begin{aligned} C_L &= 15 \text{ pF}, \\ R_L &= 100 \text{ k}\Omega \end{aligned}$	0.9	_	26.6	_	_	_	
			1.1~1.3	_	13.0	25.0	1.0	41.9	
Output enable time	t _{pZL}		1.4~1.6	_	7.4	11.4	1.0	13.4	ns
	t _{pZH}	$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65~ 1.95		5.5	7.9	1.0	8.5	
		_	2.3~2.7		3.7	4.9	1.0	5.5	
			3.0~3.6	_	3.0	4.1	1.0	4.6	
		$\begin{array}{c} C_L = 30 \text{ pF}, \\ R_L = 100 \text{ k}\Omega \end{array}$	0.9	_	36.4	_	_	_	
			1.1~1.3	_	17.9	35.8	1.0	59.1	
			1.4~1.6	_	9.8	15.3	1.0	17.8	
		$C_L = 30 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65~ 1.95	_	7.2	10.5	1.0	11.2	
			2.3~2.7	_	4.5	5.9	1.0	6.6	
	<u> </u>		3.0~3.6		3.6	4.6	1.0	5.3	

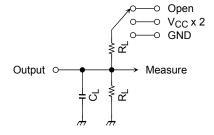
Characteristics	Symbol	Test Condition			Га = 25°C		Ta = -4	0~85°C	Unit				
Characteristics	Syllibol	rest Condition		Min	Тур.	Max	Min	Max	Offic				
		$C_L = 10 \text{ pF},$ $R_L = 100 \text{ k}\Omega$	0.9	_	168.6	_	_	_					
			1.1~1.3	_	9.5	18.4	1.0	25.2					
			1.4~1.6	_	7.5	9.5	1.0	10.6					
		$C_L = 10 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65~ 1.95		7.1	8.7	1.0	9.6					
		_	2.3~2.7	_	6.8	7.9	1.0	8.8					
			3.0~3.6		6.5	7.5	1.0	8.4					
	^t pLZ ^t pHZ	$\begin{aligned} C_L &= 15 \text{ pF}, \\ R_L &= 100 \text{ k}\Omega \end{aligned}$	0.9		201.8		_						
		$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.1~1.3	_	10.5	19.8	1.0	27.6	ns				
Output disable time			1.4~1.6		9.0	10.4	1.0	12.3					
			$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	$C_L = 15 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65~ 1.95	_	8.5	9.7	1.0	10.6	
					2.3~2.7	_	7.9	8.8	1.0	10.3			
			3.0~3.6	_	7.6	8.3	1.0	9.5					
		$\begin{aligned} C_L &= 30 \text{ pF}, \\ R_L &= 100 \text{ k}\Omega \end{aligned}$	0.9	_	251.5	_	_	_					
			1.1~1.3		14.1	23.8	1.0	31.9					
			1.4~1.6	_	13.5	14.5	1.0	16.0					
		$C_L = 30 \text{ pF},$ $R_L = 5 \text{ k}\Omega$	1.65~ 1.95		12.7	14.3	1.0	15.0					
		_	2.3~2.7		12.2	14.1	1.0	14.7					
			3.0~3.6		11.9	13.8	1.0	14.4					
Input capacitance	C _{IN}	_	3.6		3		_	_	pF				
Power dissipation capacitance	C _{PD}	(Note 14)	0.9 ~ 3.6	_	10	_	_	_	pF				

Note 14: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC\ (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$$

AC Characteristics Measurement Circuit



Characteristics	Switch
t _{pLH} , t _{pHL}	Open
t_{pLZ} , t_{pZL}	V _{CC} x 2
t _{pHZ} , t _{pZH}	GND

 $Figure 1 \quad t_{pLH}, \, t_{pHL}$

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AC Waveforms

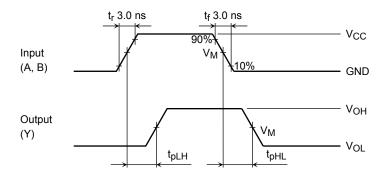
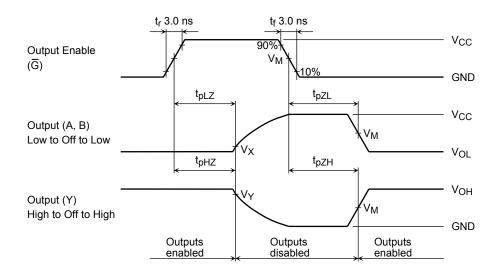


Figure 2 t_{pLH} , t_{pHL}



 $Figure 3 \quad t_{pLZ},\, t_{pHZ},\, t_{pZL},\, t_{pZH}$

UNIT			Vo	CC		
ONT	3.3±0.3 V	2.5±0.2 V	1.8±0.15 V	1.5±0.1 V	1.2±0.1 V	0.9 V
V _M	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V	V _{OL} + 0.1 V	V _{OL} + 0.1 V	V _{OL} + 0.1 V
VY	V _{OH} - 0.3 V	V _{OH} - 0.15 V	V _{OH} - 0.15 V	V _{OH} - 0.1 V	V _{OH} - 0.1 V	V _{OH} - 0.1 V

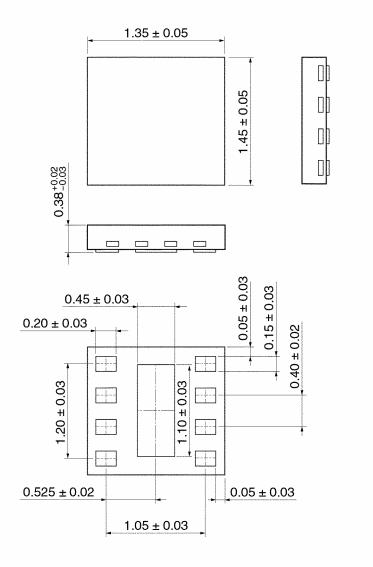
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Package Dimensions

CSON8-P-0.4 Unit: mm



Weight: 0.002 g (Typ.)

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20070701-EN GENERAL

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